# INCREASING YIELD WITH POST-FIRING ANNEAL

A proven way to improve the efficiency of under-performing screen-printed cells is to introduce a post-firing forming gas anneal. This anneal improves several cell aspects and thus increases the efficiency. The mechanisms behind this improvement are:

# **CONTACT REPAIR**

 Forming gas annealing (FGA) – helps reduce silver paste glass layer, lowering series resistance

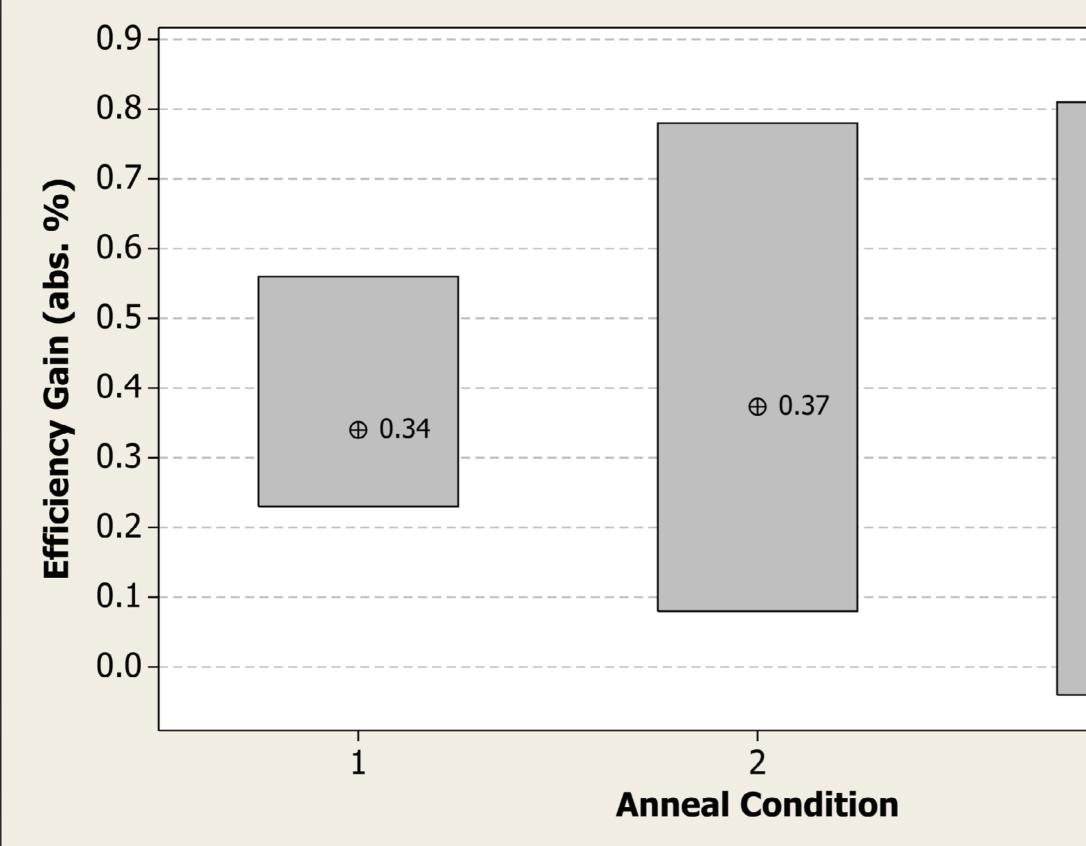
## **HYDROGEN PASSIVATION**

Hydrogen passivates defects present in the silicon surface and bulk

 For advanced cell designs, thermal annealing can help enhance passivation layers such as SiO2, AI2O3, or doped back surface field, which can significantly boost open-circuit voltage

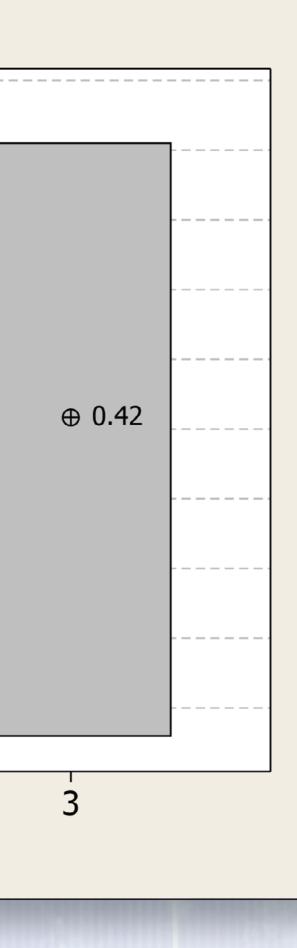
# **DEFECT REPAIR**

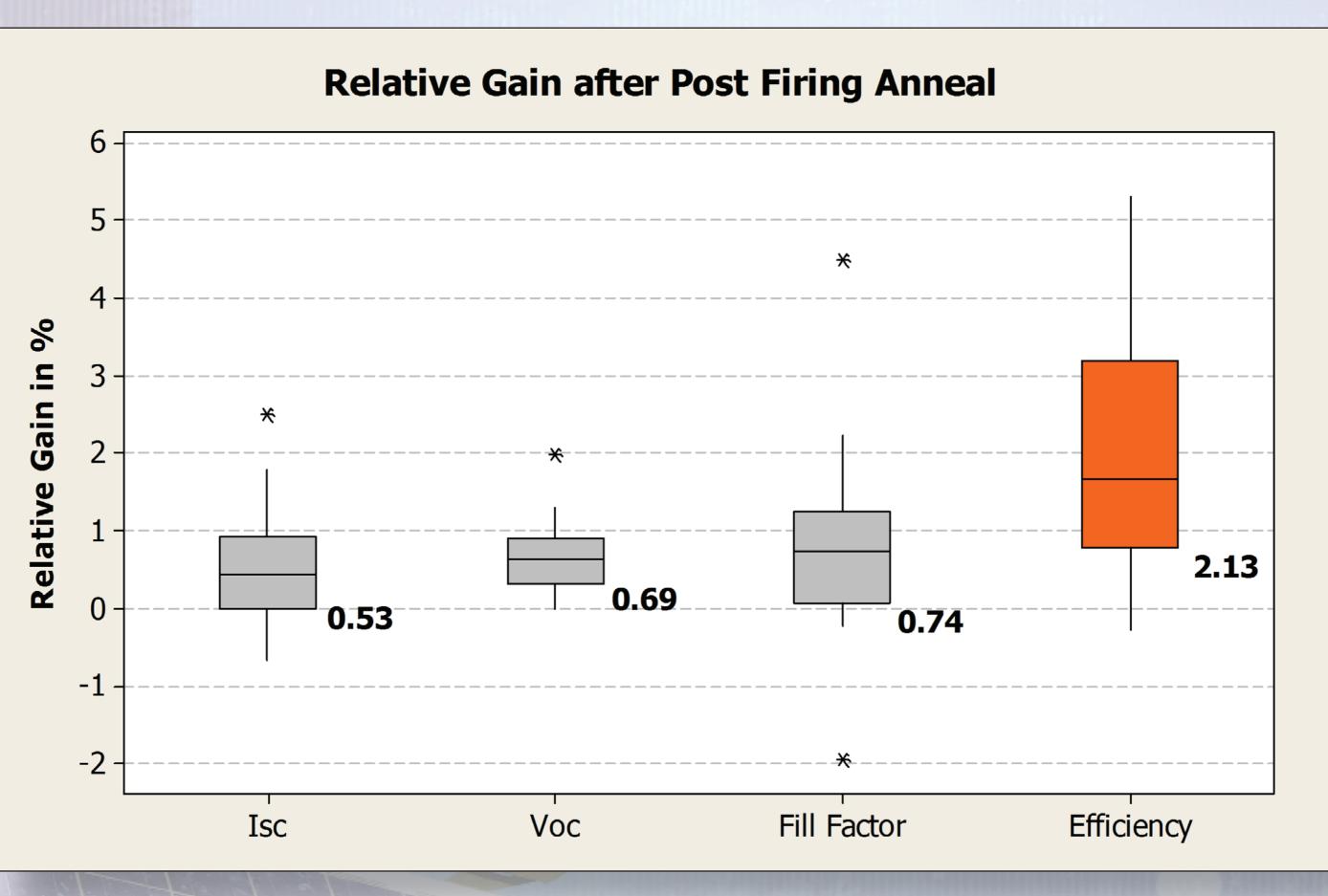
Heat can re-crystallize and burn-out defects in the silicon surface or bulk



## **Post Firing Anneal Efficiency Gain**

Efficiency gain after post-firing anneal for different anneal conditions





Relative gain after post-firing anneal for the most important cell metrics.

# TESTS HAVE SHOWN THAT AN EFFICIENCY GAIN OF UP TO 0.8% ABSOLUTE IS POSSIBLE. THE AVERAGE GAIN WAS 0.3% ABSOLUTE.

This improvement is due to an improvement in all cell characteristics as shown in the graph. Since the post-firing anneal primarily has an effect on the SiN passivated front side of a standard cell it is expected that the effect would be even larger on double sided passivated cells.

The key to maximizing Post-Firing Anneal gains is a high degree of profile flexibility. This profile flexibility can be achieved via the use of infrared lamps. Low cost of ownership is possible while maintaining low oxygen levels (<100ppm) by using small amounts of forming gas.